	Reverse Voltage	V_R	6	V
	Power Dissipation	P_D	100	mW
Detector	Output Voltage	V_O	35	V
	Supply Voltage	V_{CC}	35	V
	Power Dissipation	P_C	400	mW
Isolation Voltage		V_{iso}	3750	Vrms
Operating Temperature		T_{opr}	-40~110	
Junction Temperature		T_j	125	
Storage Temperature		T_{stg}	-55~125	
Total Power Dissipation		P_{tot}	500	mW
Soldering Temperature		T_{sol}	260	

: μ

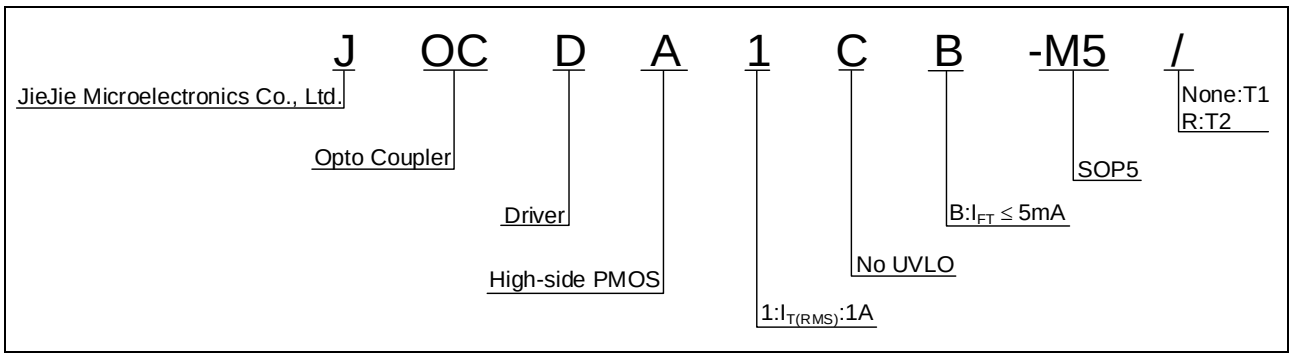
:

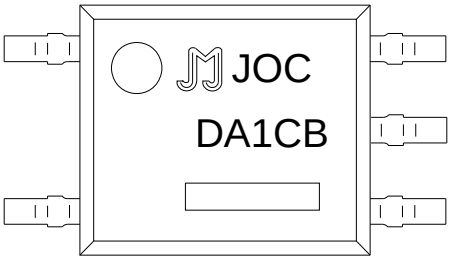
(Temperature=25°C)

Parameter		Symbol	Condition	Min.	Typ.	Max.	Unit
Input	Forward Voltage	V_F	I_F=10mA	-	1.35	1.6	V
	Reverse Current	I_R	V_R=6V	-	-	1	μA
	Terminal Capacitance	C_t	V=0,f=1MHz	-	60	-	pF
Output	Peak High-level Output Current	I_{OPH}	V_O=V_{CC}-1.5V	-0.3	-	-	A
			V_O=V_{CC}-3V	-0.8	-	-	A
	Peak Low-level Output Current	I_{OPL}	V_O=V_{EE}+1.5V	0.3	-	-	A
			V_O=V_{EE}+3V	0.8	-	-	A
	High Level Supply Current	I_{CCH}	I_F=10mA V_{CC}=30V, V_O=Open,	-	1.2	2	mA
	Low Level Supply Current	I_{CCL}	I_F=0mA , V_{CC}=30V, V_O=Open,	-	1.1	2	mA
	High Level Output Voltage	V_{OH}	I_O=-100mA	V_{CC}-0.6	V_{CC}-0.2	-	V
	Low Level Output Voltage	V_{OL}	I_O=100mA	-	0.075	0.2	V
	Threshold Input Current	I_{FLH}	V_O 5V	-	2.5	5	mA
	Threshold Input Voltage	V_{FHL}	V_O 5V	0.8	-	-	V
	Supply Voltage	V_{CC}	-	10	-	30	V

Parameter	Symbol	Condition	Min.	T	ax.	Unit
Propagation Delay Time to High Output Level	t_{PLH}	R_g=47Ω, C_g=3nF, f=10kHz, Duty Cycle=50%, I_F=7mA, V_{CC}=30V	50		00	
Propagation Delay Time to Low Output Level	t_{PHL}		50		00	
Pulse Width Distortion	PWD		-	-	70	
Propagation Delay Difference Between Any Two Parts	t_{PHL}- t_{PLH}		-100	-	100	
Output Rise Time (10 to 90%)	t_r	R_g=47Ω, C_g=3nF, I_F=0→7mA, V_{CC}=30V				ns

Characteristics	Symbol	Min.	Typ.	Max.	Unit
Input On-state Current	$I_{F(ON)}$	7	-	10	mA
Input Off-state Voltage	$V_{F(OFF)}$	0	-	0.8	V
Supply Voltage	V_{CC}	10	-	30	V
Operating Frequency	f	-	-	50	kHz


J
OC
D
A
1
C
B
-M5
/
JieJie Microelectronics Co., Ltd.
Opto Coupler
Driver
High-side PMOS
1:I$_{T(RMS)}$:1A
No UVLO
B:I$_{FT}$ ≤ 5mA
SOP5
None:T1
R:T2


JOC
DA1CB


Production Information Code

FIG.1: Forward Current vs. Forward Voltage

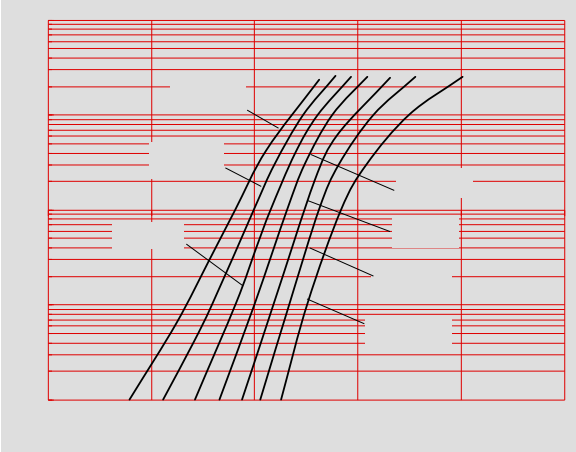


FIG.2: Max. Allowable LED Forward Current vs. Ambient Temperature

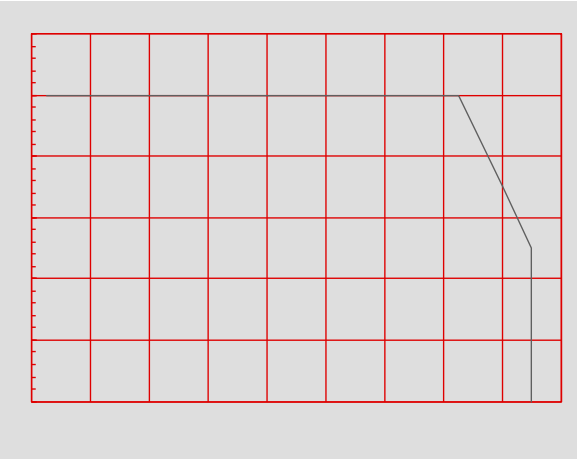


FIG.3: Collector Power Dissiption vs. Ambient Temperature

FIG.4: Threshold Input Current vs. Ambient Temperature

FIG.7: Low-level Output Voltage vs. Ambient Temperature

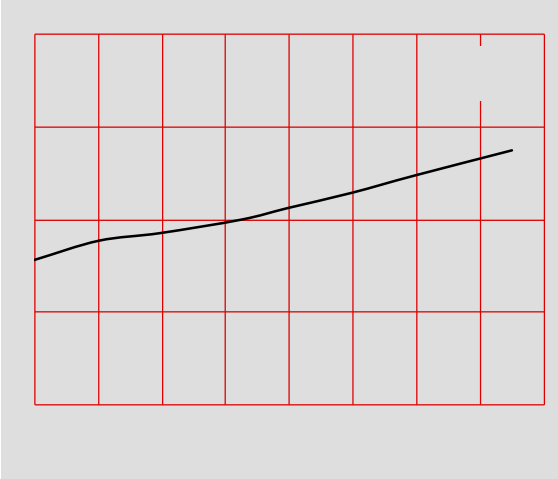


FIG.8: High-level Output Voltage vs. Ambient Temperature

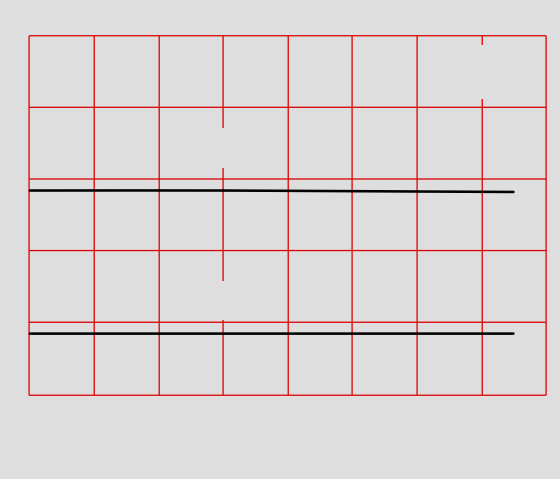


FIG.9: Low-level Output Voltage vs. Peak Low-level Output Current

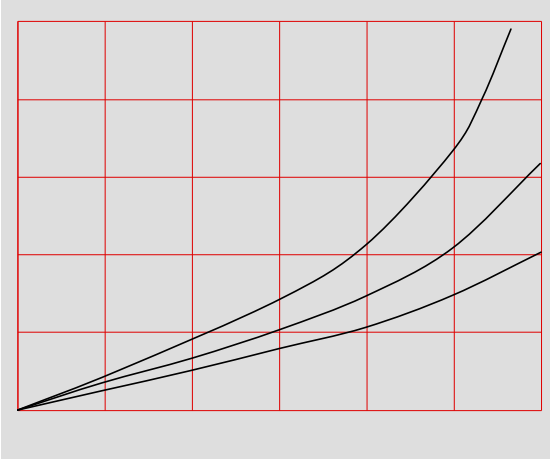
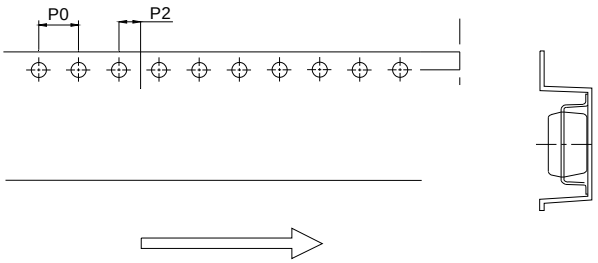


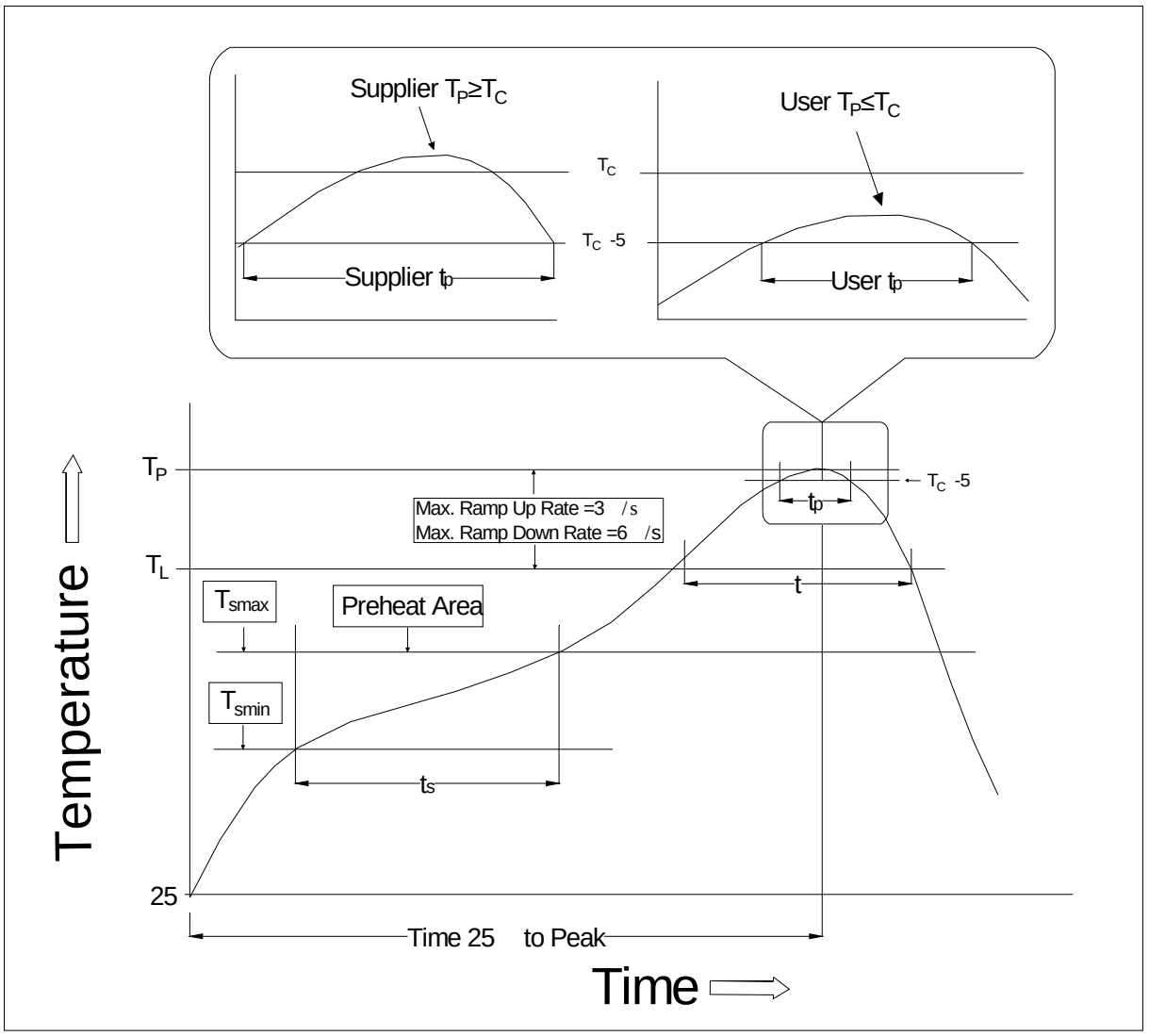
FIG.10: High-level Output Voltage Drop vs. Peak High-level Output Current

FIG.13: Propagation Delay Time,Pulse Width Distortion vs. Supply Voltage

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A						
B						
C						
D						
E						
F	0.34			0.013		
G						
H						
I	2.00			0.079		
J			0.55	0.010		

Option None





Profile Feature	Sn-Pb Assembly Profile	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	100	150
Temperature Max. (Tsmax)	150	200
Time (ts) from (Tsmin to Tsmax)	60-120 seconds	60-120 seconds
Ramp-up Rate (tL to tP)	3 /second max.	3 /second max.
Liquidus Temperature (TL)	183	217
Time (tL) Maintained Above (TL)	60-150 seconds	60-150 seconds
Peak Body Package Temperature	235 +0 /-5	260 +0 /-5
Time (tP) within 5 of 260	10 seconds	10 seconds
Ramp-down Rate (TP to TL)	3-6 /second	3-6 /second
Time 25 to Peak Temperature	6 minutes max.	8 minutes max.

Note:

1. Reflow soldering is recommended at the temperatures and times shown, no more than three times.

2. Avoid direct contact between the epoxy body and any tools or surfaces exceeding its maximum storage temperature.

3. Application of pressure on the epoxy body is prohibited at elevated temperatures. In specific scenarios, any applied force must not exceed 2.5N.

4. Ensure the component has cooled to ambient temperature before proceeding with any subsequent manufacturing steps.

5. The component has a shelf life of one year when stored under standard conditions.

6. Recommend storage Temp.: 0~40°C;

Recommend storage humidity: <60%;

MSL level: MSL 1

Information furnished in this document is believed to be accurate and reliable. However, Jiangsu JieJie Microelectronics Co., Ltd. assumes no responsibility for the consequences of use without consideration for such information nor use beyond it. Information mentioned in this document is subject to change without notice, apart from that when an agreement is signed, Jiangsu JieJie complies with the agreement.

Products and information provided in this document have no infringement of patents. Jiangsu JieJie assumes no responsibility for any infringement of other rights of third parties which may result from the use of such products and information. This document supersedes and replaces all information previously supplied.

is a registered trademark of Jiangsu JieJie Microelectronics Co., Ltd.

Copyright © 2026 Jiangsu JieJie Microelectronics Co., Ltd. All rights reserved.